

/ Descriptions

PDFN3×3A-8L N MOS
N-Channel Enhancement Mode Field Effect Transistor in a PDFN3×3A-8L Plastic Package.

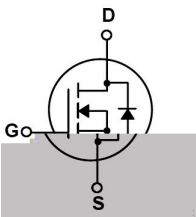
/ Features

$V_{DS} (V) = 30V$ $I_D = 76A (V_{GS} = 20V)$
 $R_{DS(ON)}@10V \ 3.5m \ (Typ.3.3m \)$
 $R_{DS(ON)}@4.5V \ 6.5m \ (Typ.4.7m \)$
HF Product.

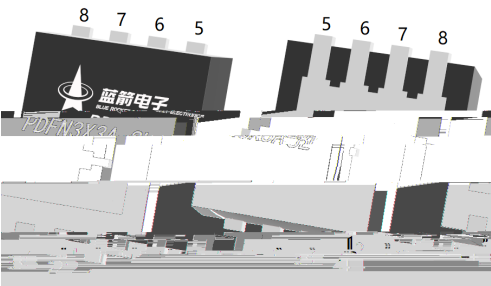
/ Applications

Load Switch Applications,Battery Power Management.

/ Equivalent Circuit



/ Pinning



出脚	定义
Pin1	S
Pin2	S
Pin3	S
Pin4	G
Pin5	D
Pin6	D
Pin7	D
Pin8	D

/ Marking

See Marking Instructions.

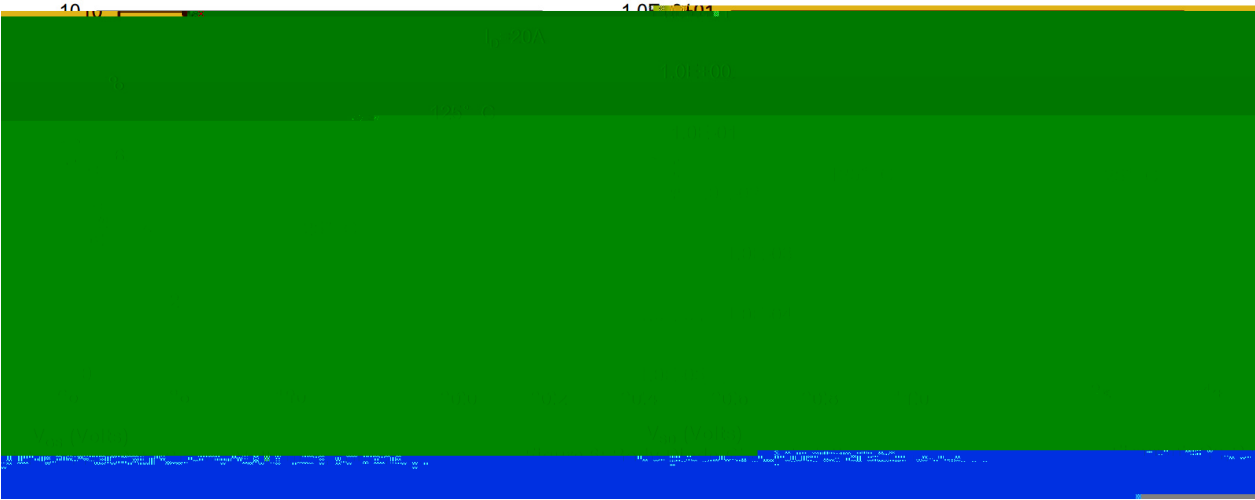
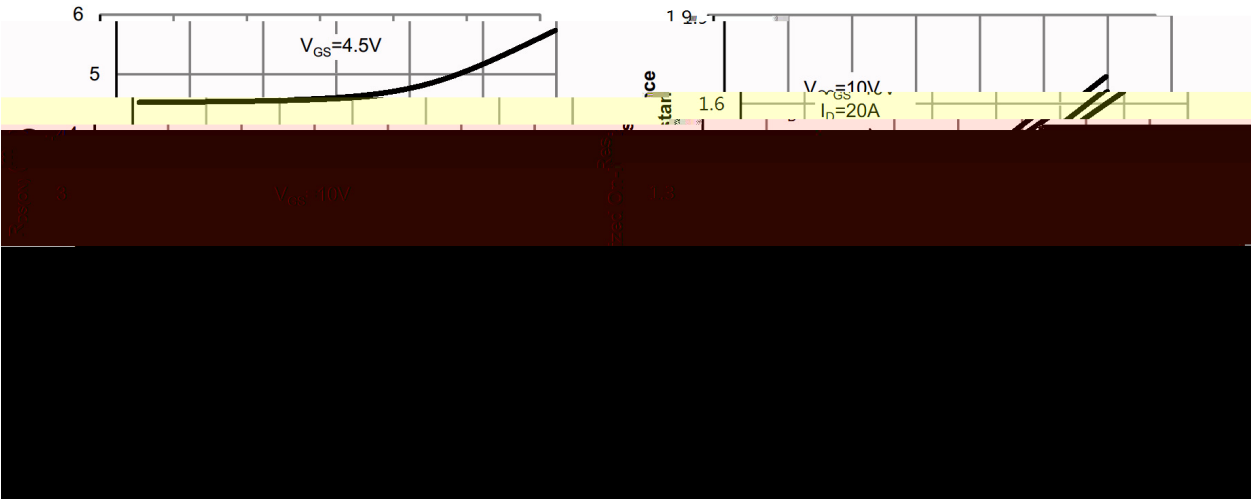
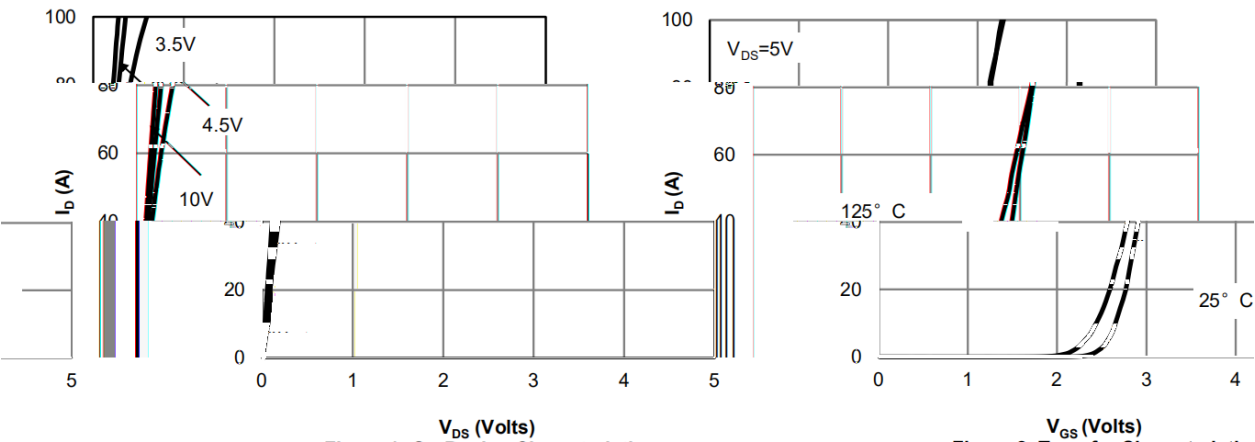
/ Absolute Maximum Ratings(Ta=25)

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	30	V
Drain Current		$I_D(T_c=25)$	76	A
Drain Current - Pulsed		I_{DM}	190	A
Gate-Source Voltage		V_{GS}	± 20	V
Single Pulsed Avalanche Energy		E_{AS}	449	mJ
Avalanche Current		I_{AS}	33.5	A
Power Dissipation		$P_D(T_c=25)$	35	W
Operating and Storage Temperature Range		T_J, T_{stg}	-55 to 150	
Junction-to-Ambient	$t \leq 10$	R_{JA}	42	/W
Junction-to-Ambient	Steady-State		78	
Junction-to-Case	Steady-State	R_{JC}	3.6	

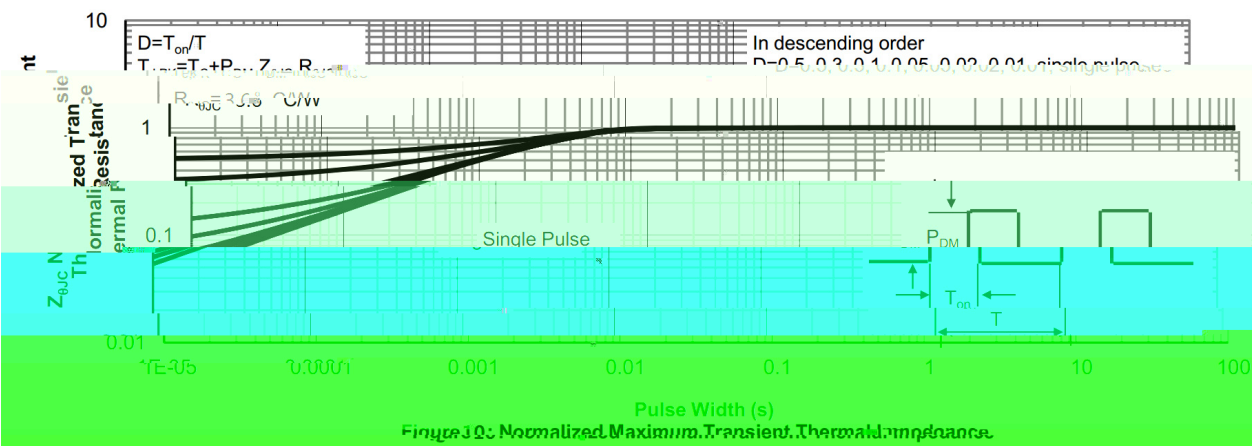
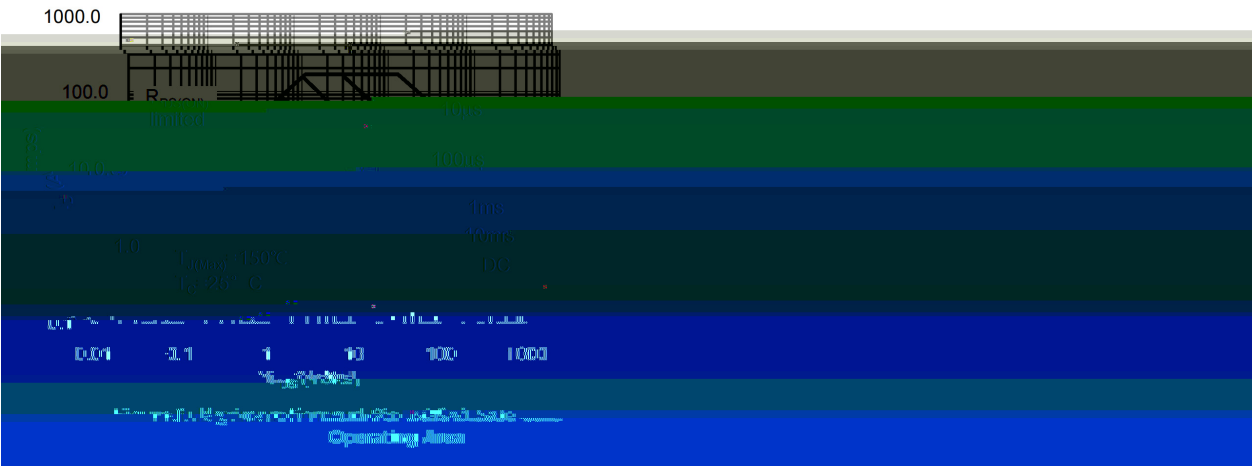
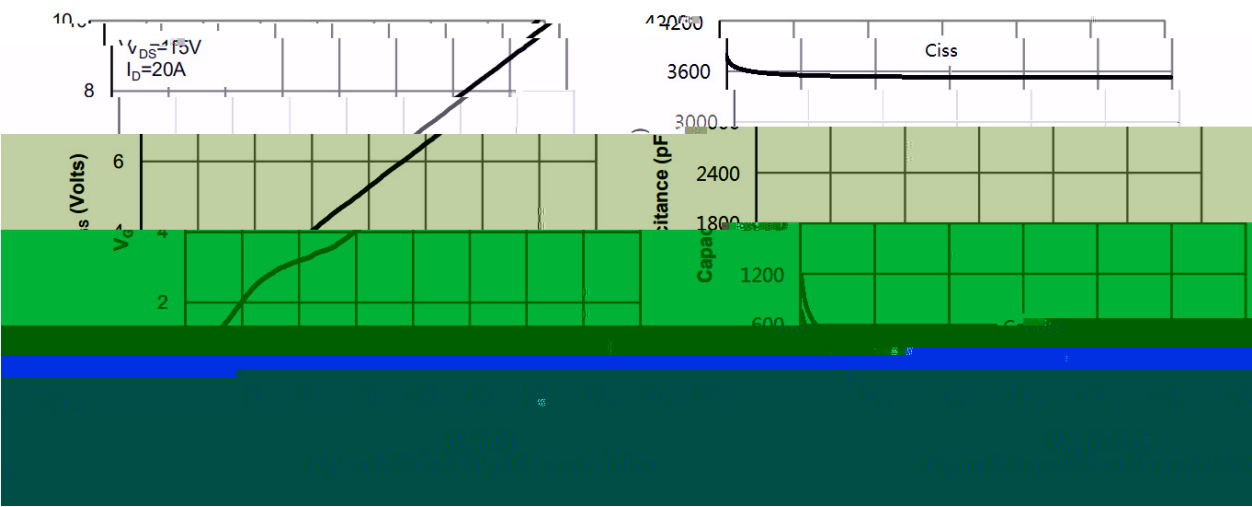
/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V$ $I_D=250\text{ A}$	30	35		V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=30V$ $V_{GS}=0V$			1	A
Gate-Body Leakage Current Forward	I_{GSS}	$V_{GS}=\pm 20V$ $V_{DS}=0V$			± 0.1	A
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=250\text{ A}$	1.0	1.5	3.0	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V$ $I_D=20A$		3.3	3.5	m
		$V_{GS}=4.5V$ $I_D=10A$		4.7	6.5	m
Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS}=0V$ $I_S=1A$			1.2	V
Input Capacitance	C_{iss}	$V_{DS}=25V$ $V_{GS}=0V$ $f=1.0MHz$		3470		pF
Output Capacitance	C_{oss}			270		
Reverse Transfer Capacitance	C_{rss}			240		
Gate resistance	R_g	$V_{GS}=0V$ $V_{DS}=0V$ $f=1MHz$		1.7		
Total Gate Charge	$Q_{g(10V)}$	$V_{GS}=10V$ $V_{DS}=15V$ $I_D=20A$		80		nC
Total Gate Charge	$Q_{g(4.5V)}$			35		
Gate Source Charge	Q_{gs}			13		
Gate Drain Charge	Q_{gd}			13		
Turn-On Delay Time	$t_{d(on)}$	$V_{GS}=10V$ $V_{DS}=15V$ $R_L=0.75$ $R_{GEN}=3.0$		6.7		ns
Turn-On Rise Time	t_r			3.8		
Turn-Off Delay Time	$t_{d(off)}$			32		
Turn-Off Fall Time	t_f			5.2		

/ Electrical Characteristic Curve



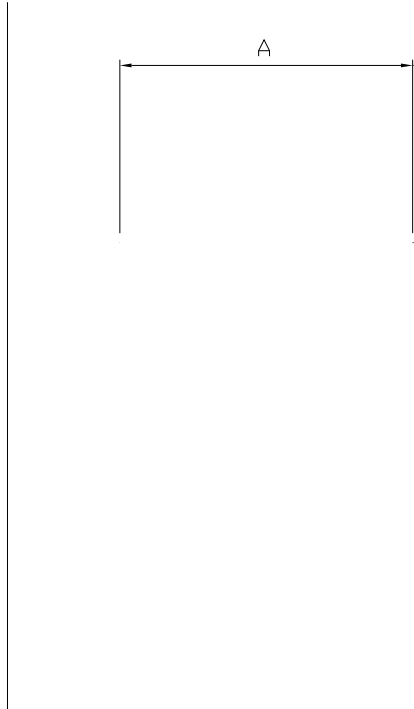
/ Electrical Characteristic Curve



/ Package Dimensions

PDFN3X3A-8L

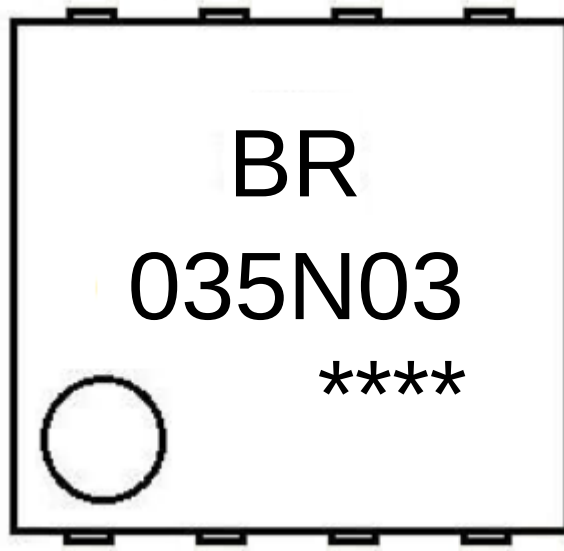
Unit:mm



Dimensions In
 Mi

Rev.00 202011

/ Marking Instructions



BR

035N03

Note:

BR: Company Code

035N03: Product Type Code

****: Lot No. Code, code change with Lot No

() / Temperature Profile for IR Reflow Soldering(Pb-Free)

- Note:
- 1

150 180 60 90sec;

1.Preheating:150~180 , Time:60~90sec.
- 2

245±5 5±0.5sec;

2.Peak Temp.:245±5 , Duration:5±0.5sec.
- 3

2 10 /sec.

3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

260±5 10±1 sec. Temp.:260±5 Time:10±1 sec

/ Packaging SPEC.

/ REEL